

Silicon Carbide (SiC) MOSFET – EliteSiC, 80 mohm, 1200 V, M1, Die

NTC080N120SC1

Description

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

Features

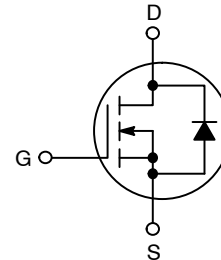
- 1200 V @ $T_J = 175^\circ\text{C}$
- Typ $R_{DS(on)} = 80\text{ m}\Omega$ at $V_{GS} = 20\text{ V}$, $I_D = 20\text{ A}$
- High Speed Switching with Low Capacitance
- 100% UIL Tested
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb-Free 2LI (on second level interconnection)

Applications

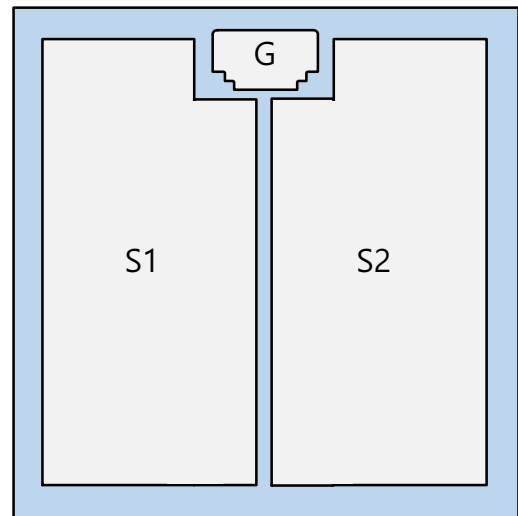
- Industrial Motor Drive
- UPS
- Boost Inverter
- PV Charger

$V_{(BR)DSS}$	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
1200 V	110 m Ω @ 20 V	31 A

N-CHANNEL MOSFET



DIE DIAGRAM

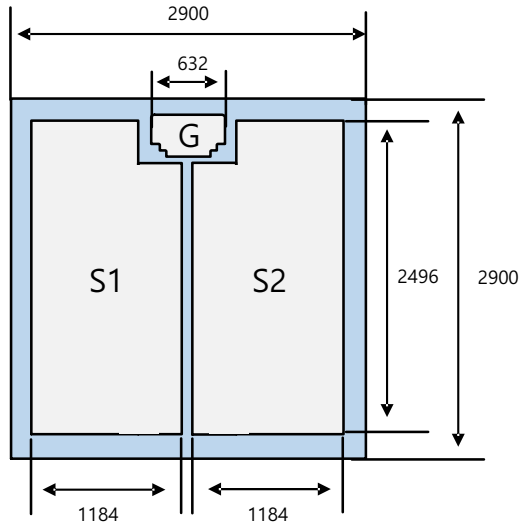


Die Information

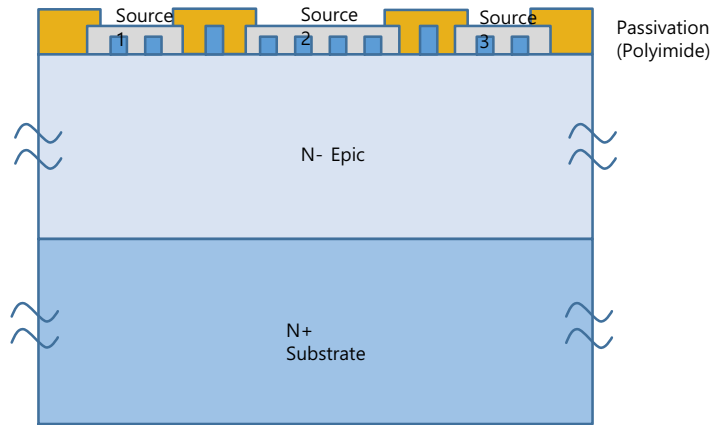
• Wafer Diameter	6 inch
• Die Size	2,900 x 2,900 μm
• Metallization	
· Top	Ti/TiN/Al 5 μm
· Back	Ti/V/Ni/Ag
• Die Thickness	Typ. 200 μm
• Gate Pad Size	632 x 242.5 μm

NTC080N120SC1

Die Layout



Die Cross Section



Passivation Information

- Passivation Material: Polyimide (PSPi)
- Passivation Type: Local Passivation
- Passivation Thickness 10 μm
- : Passivation Area

Die Layout

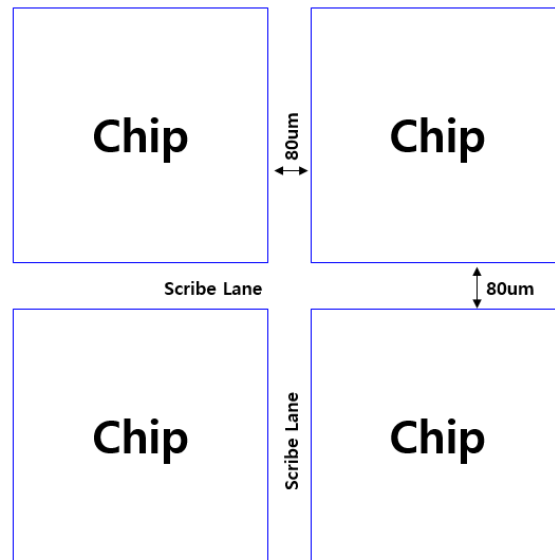


Figure 1. Bare Die Dimensions

NTC080N120SC1

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	1200	V
Gate-to-Source Voltage			V _{GS}	-15/+25	V
Recommended Operation Values of Gate-to-Source Voltage	T _C < 175°C		V _{GSop}	-5/+20	V
Continuous Drain Current R _{θJC}	Steady State	T _C = 25°C	I _D	31	A
Power Dissipation R _{θJC}			P _D	178	W
Continuous Drain Current R _{θJC}	Steady State	T _C = 100°C	I _D	22	A
Power Dissipation R _{θJC}			P _D	89	W
Pulsed Drain Current (Note 2)	T _C = 25°C		I _{DM}	132	A
Single Pulse Surge Drain Current Capability	T _C = 25°C, t _p = 10 μs, R _G = 4.7 Ω		I _{DSC}	132	A
Operating Junction and Storage Temperature Range			T _J , T _{stg}	-55 to +175	°C
Source Current (Body Diode)			I _S	18	A
Single Pulse Drain-to-Source Avalanche Energy (I _{L(pk)} = 18.5 A, L = 1 mH) (Note 3)			E _{AS}	171	mJ

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Note 1)	R _{θJC}	0.84	°C/W

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. E_{AS} of 171 mJ is based on starting T_J = 25°C; L = 1 mH, I_{AS} = 18.5 A, V_{DD} = 120 V, V_{GS} = 18 V.

NTC080N120SC1

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
-----------	--------	-----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 1 mA	1200	–	–	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I _D = 1 mA, referenced to 25°C	–	700	–	mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 1200 V, T _J = 25°C	–	–	100	μA
		V _{GS} = 0 V, V _{DS} = 1200 V, T _J = 175°C	–	–	250	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = +25/-15 V, V _{DS} = 0 V	–	–	±1	μA

ON CHARACTERISTICS

Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = 5 mA	1.8	2.7	4.3	V
Recommended Gate Voltage	V _{GOP}		–5	–	+20	V
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 20 V, I _D = 20 A, T _J = 25°C	–	80	110	mΩ
		V _{GS} = 20 V, I _D = 20 A, T _J = 150°C	–	114	–	
Forward Transconductance	g _{FS}	V _{DS} = 20 V, I _D = 20 A	–	13	–	S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 800 V	–	1112	–	pF
Output Capacitance	C _{OSS}		–	80	–	
Reverse Transfer Capacitance	C _{RSS}		–	6.5	–	
Total Gate Charge	Q _{G(tot)}	V _{GS} = –5/20 V, V _{DS} = 600 V, I _D = 20 A	–	56	–	nC
Gate-to-Source Charge	Q _{GS}		–	11	–	
Gate-to-Drain Charge	Q _{GD}		–	12	–	
Gate Resistance	R _G	f = 1 MHz	–	1.7	–	Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	t _{d(on)}	V _{GS} = –5/20 V, V _{DS} = 800 V, I _D = 20 A, R _G = 4.7 Ω, Inductive Load	–	13	–	ns
Rise Time	t _r		–	20	–	
Turn-Off Delay Time	t _{d(off)}		–	22	–	
Fall Time	t _f		–	10	–	
Turn-On Switching Loss	E _{ON}		–	258	–	μJ
Turn-Off Switching Loss	E _{OFF}		–	52	–	
Total Switching Loss	E _{TOT}		–	311	–	

DRAIN-SOURCE DIODE CHARACTERISTICS

Continuous Drain-to-Source Diode Forward Current	I _{SD}	V _{GS} = –5 V	–	–	18	A
Pulsed Drain-to-Source Diode Forward Current (Note 2)	I _{SDM}	V _{GS} = –5 V	–	–	132	A
Forward Diode Voltage	V _{SD}	V _{GS} = –5 V, I _{SD} = 10 A	–	4	–	V
Reverse Recovery Time	t _{RR}	V _{GS} = –5/20 V, I _{SD} = 20 A, dI _S /dt = 1000 A/μs	–	16	–	ns
Reverse Recovery Charge	Q _{RR}		–	62	–	nC
Reverse Recovery Energy	E _{REC}		–	5	–	μJ
Peak Reverse Recovery Current	I _{RRM}		–	8	–	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

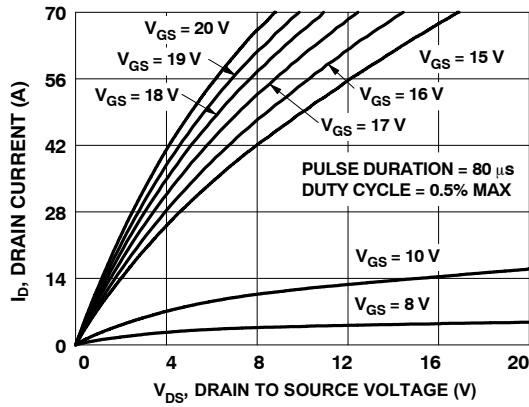


Figure 2. On Region Characteristics

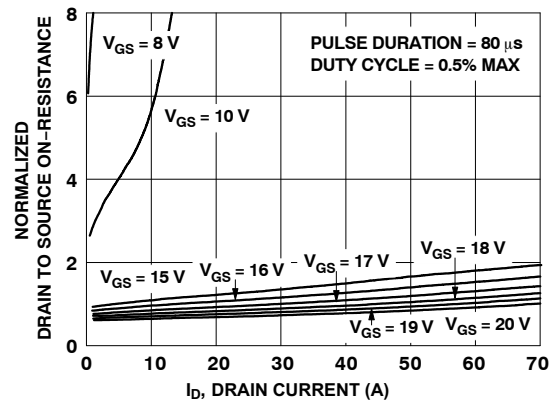


Figure 3. Normalized On-Resistance vs. Drain Current and Gate Voltage

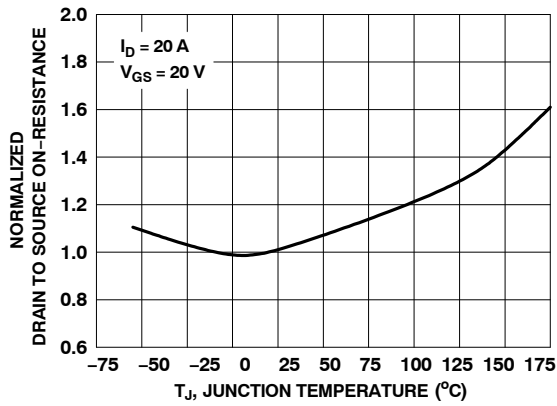


Figure 4. Normalized On Resistance vs. Junction Temperature

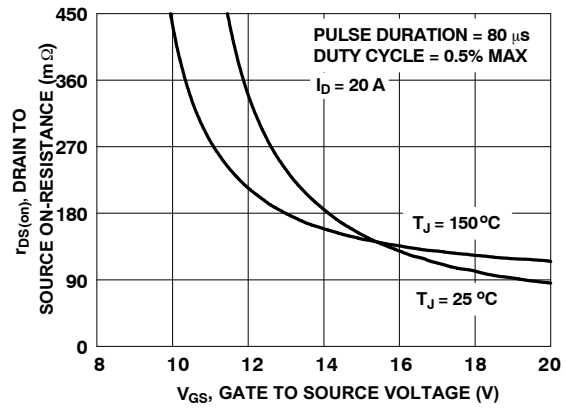


Figure 5. On-Resistance vs. Gate-to-Source Voltage

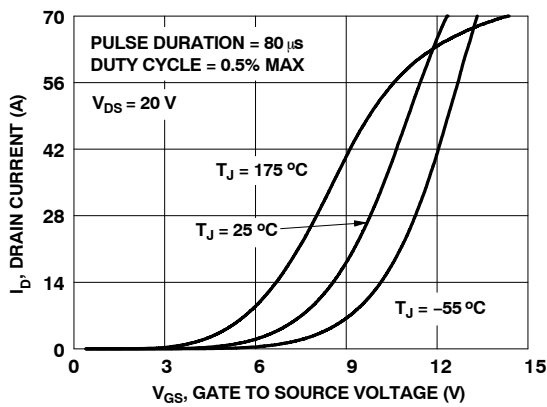


Figure 6. Transfer Characteristics

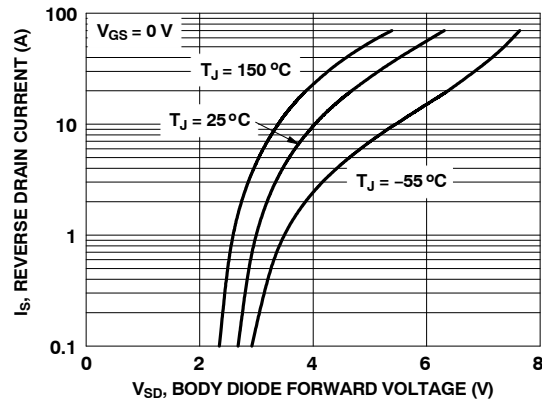


Figure 7. Source-to-Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

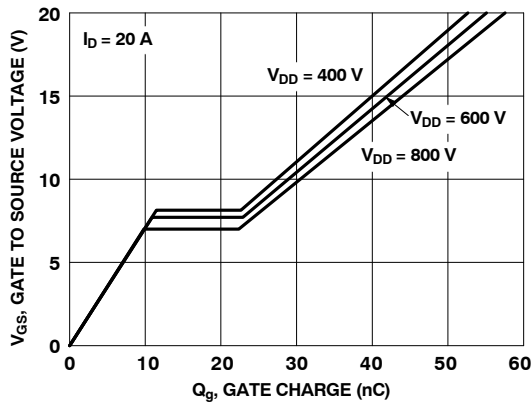


Figure 8. Gate Charge Characteristics

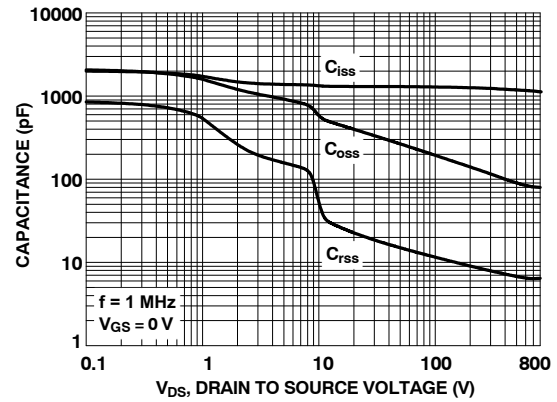


Figure 9. Capacitance vs. Drain-to-Source Voltage

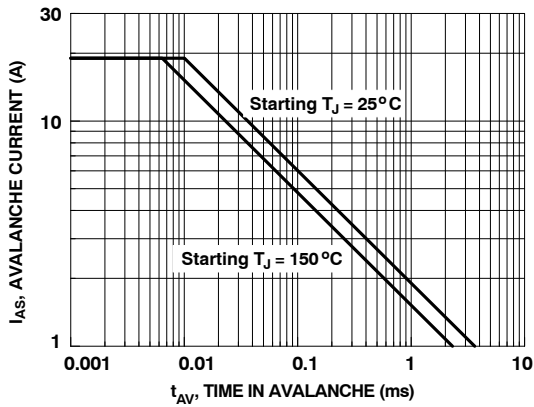


Figure 10. Unclamped Inductive Switching Capability

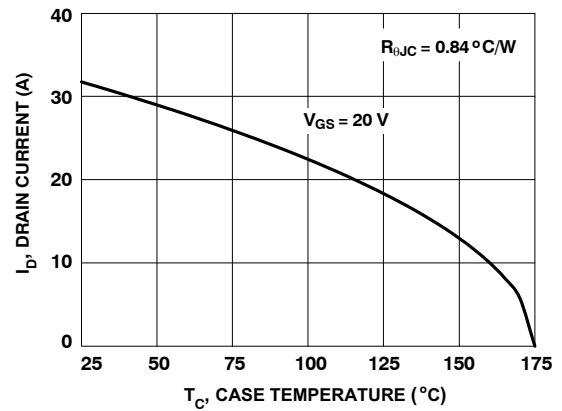


Figure 11. Maximum Continuous Drain Current vs. Case Temperature

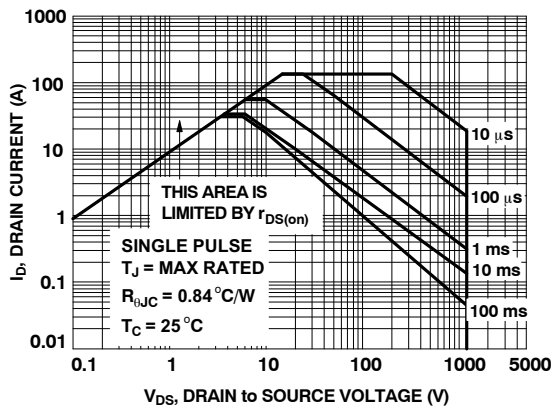


Figure 12. Forward Bias Safe Operating Area

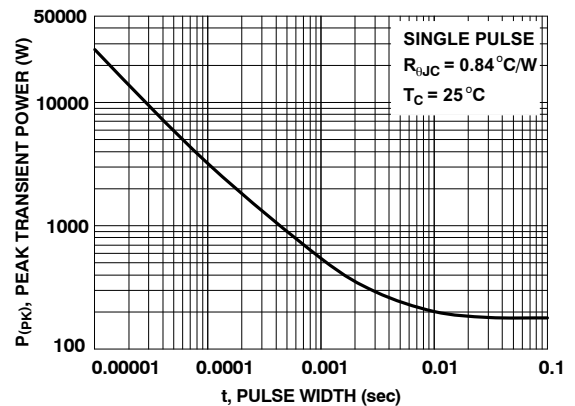


Figure 13. Single Pulse Maximum Power Dissipation

NTC080N120SC1

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

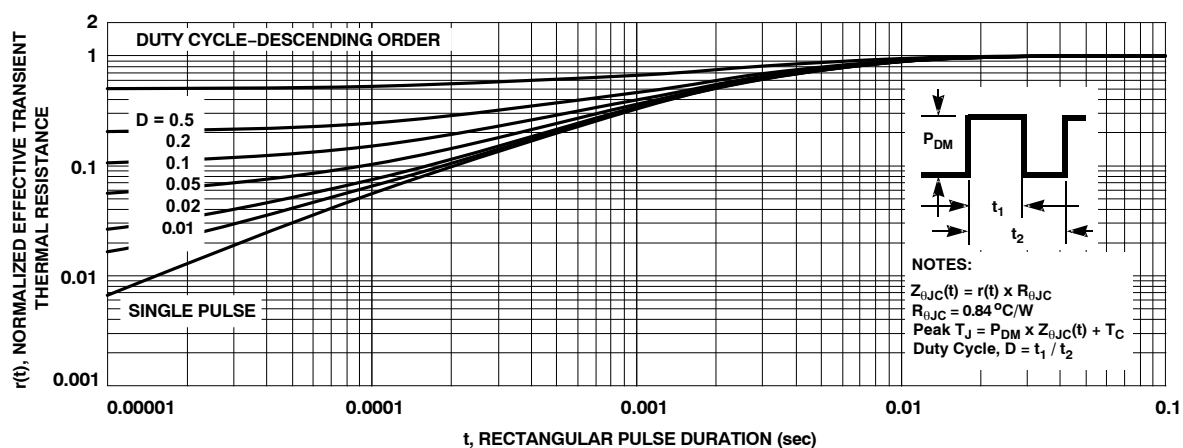


Figure 14. Junction-to-Case Transient Thermal Response Curve

ORDERING INFORMATION AND PACKAGE MARKING

Orderable Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NTC080N120SC1	N/A	Die	Wafer	N/A	N/A	N/A

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales